



### General Description

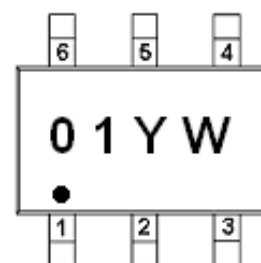
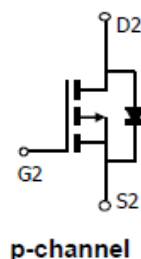
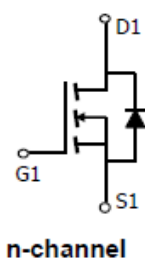
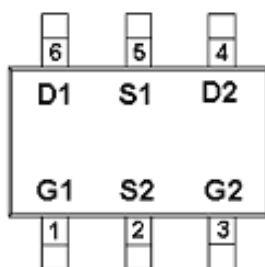
AFC6601, N & P Pair enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent  $R_{DS(ON)}$ , low gate charge.

These devices are particularly suited for low voltage power management, and low in-line power loss are needed in commercial industrial surface mount applications.

### Features

- N-Channel  
30V/3.4A,  $R_{DS(ON)}=46m\Omega@V_{GS}=10V$   
30V/3.0A,  $R_{DS(ON)}=58m\Omega@V_{GS}=4.5V$   
30V/2.0A,  $R_{DS(ON)}=125m\Omega@V_{GS}=2.5V$
- P-Channel  
-30V/-2.6A,  $R_{DS(ON)}=110m\Omega@V_{GS}=-10.0V$   
-30V/-2.0A,  $R_{DS(ON)}=125m\Omega@V_{GS}=-4.5V$   
-30V/-1.2A,  $R_{DS(ON)}=150m\Omega@V_{GS}=-2.5V$
- Super high density cell design for extremely low  $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- TSOP-6 package design

### Pin Description ( TSOP-6 )



### Application

- Power Management in Note book
- Portable Equipment
- Battery Powered System
- DC/DC Converter
- Load Switch
- DSC
- LCD Display inverter



**Pin Define**

Pin	Symbol	Description
1	G1	Gate 1
2	S2	Source 2
3	G2	Gate 2
4	D2	Drain 2
5	S1	Source 1
6	D1	Drain1

**Ordering Information**

Part Ordering No.	Part Marking	Package	Unit	Quantity
AFC6601TS6RG	01YW	TSOP-6	Tape & Reel	3000 EA

- ※ 01 parts code
- ※ Y year code ( 0 ~ 9 )
- ※ W week code ( A ~ Z = 1 ~ 26 / a ~ z = 27 ~ 52 )
- ※ AFC6601TS6RG : 7" Tape & Reel ; Pb- Free ; Halogen -Free

**Absolute Maximum Ratings**

(T<sub>A</sub>=25°C Unless otherwise noted)

Parameter	Symbol	Value		Unit
		N-Channel	P-Channel	
Drain-Source Voltage	V <sub>DSS</sub>	30	-30	V
Gate -Source Voltage	V <sub>GSS</sub>	±20	±12	V
Continuous Drain Current(T <sub>J</sub> =150°C)	I <sub>D</sub>	T <sub>A</sub> =25°C	3.4	A
		T <sub>A</sub> =70°C	2.8	
Pulsed Drain Current	I <sub>DM</sub>	15	-15	A
Continuous Source Current(Diode Conduction)	I <sub>S</sub>	1.5	-1.5	A
Power Dissipation	P <sub>D</sub>	T <sub>A</sub> =25°C	2.0	W
		T <sub>A</sub> =70°C	1.3	
Operating Junction Temperature	T <sub>J</sub>	150		°C
Storage Temperature Range	T <sub>STG</sub>	-55/150		°C
Thermal Resistance-Junction to Ambient	R <sub>θJA</sub>	120		°C/W



**Electrical Characteristics ( N-Channel )**

(T<sub>A</sub>=25°C Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	30			V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	0.6		1.4	
Gate Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±12V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =24V, V <sub>GS</sub> =0V			1	μA
		V <sub>DS</sub> =24V, V <sub>GS</sub> =0V T <sub>J</sub> =85°C			30	
On-State Drain Current	I <sub>D(on)</sub>	V <sub>DS</sub> ≥5V, V <sub>GS</sub> =4.5V	30			A
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =3.4A		36	46	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =3.0A		42	58	
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =2.0A		105	125	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =1.6A		20		S
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =1.7A, V <sub>GS</sub> =0V		0.8	1.2	V
<b>Dynamic</b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =15V, V <sub>GS</sub> =4.5V I <sub>D</sub> ≅3.6A		2.3	3	nC
Gate-Source Charge	Q <sub>gs</sub>			1.0		
Gate-Drain Charge	Q <sub>gd</sub>			0.6		
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V f=1MHz		280		pF
Output Capacitance	C <sub>oss</sub>			40		
Reverse Transfer Capacitance	C <sub>rss</sub>			20		
Turn-On Time	t <sub>d(on)</sub>	V <sub>DD</sub> =15V, R <sub>L</sub> =15Ω I <sub>D</sub> ≅1.0A, V <sub>GEN</sub> =10V R <sub>G</sub> =6Ω		10	15	ns
	t <sub>r</sub>			12	20	
Turn-Off Time	t <sub>d(off)</sub>				15	
	t <sub>f</sub>			10	15	



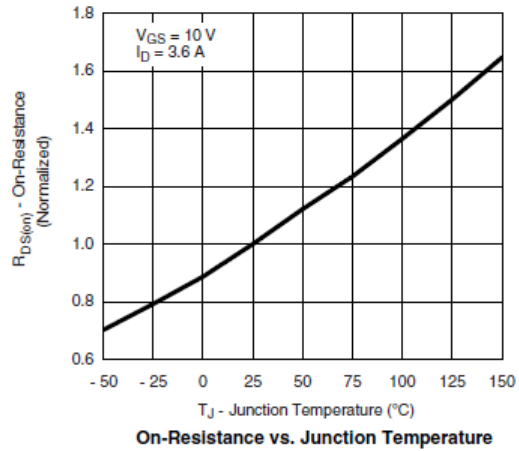
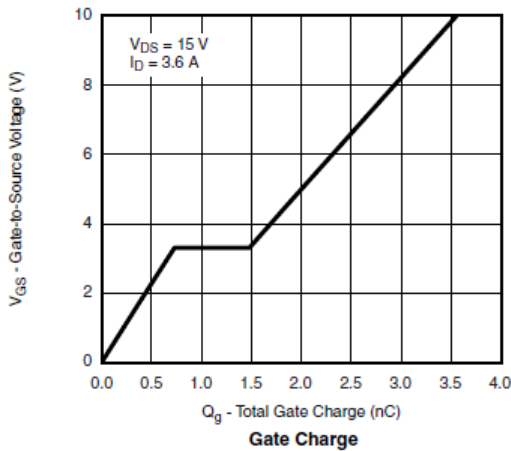
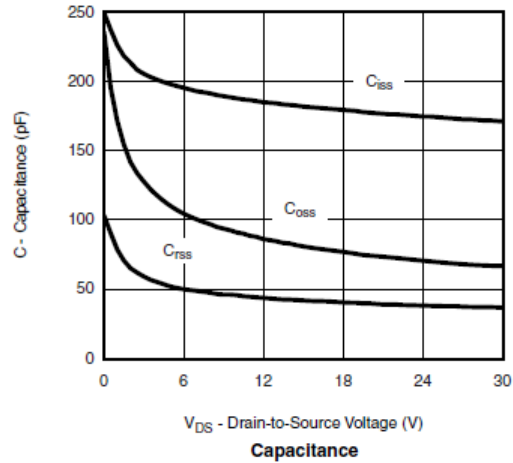
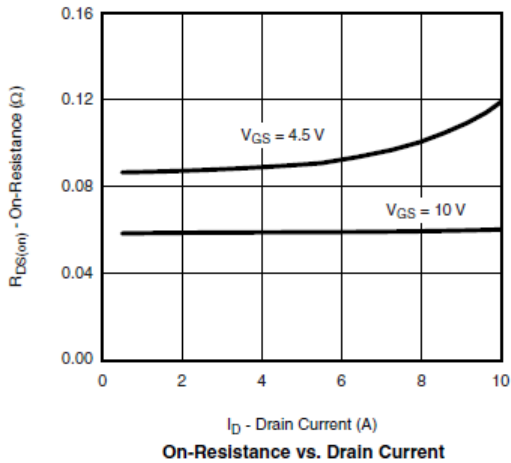
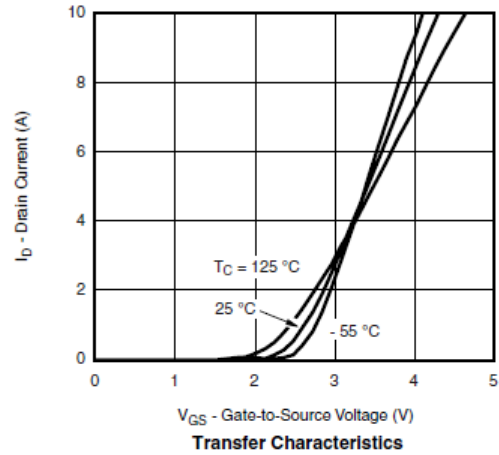
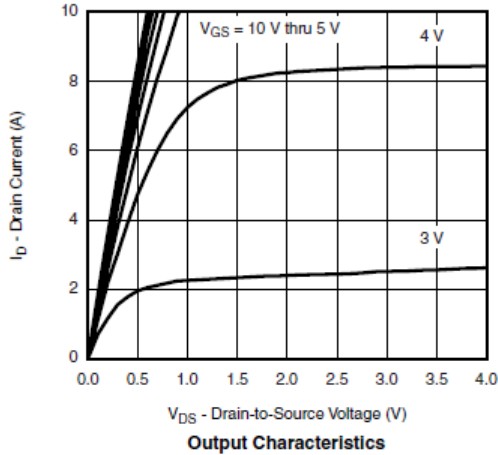
**Electrical Characteristics ( P-Channel )**

(T<sub>A</sub>=25°C Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250μA	-30			V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA	-0.6		-1.4	
Gate Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±12V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-24V, V <sub>GS</sub> =0V			-1	μA
		V <sub>DS</sub> =-24V, V <sub>GS</sub> =0V T <sub>A</sub> =85°C			-30	
On-State Drain Current	I <sub>D(on)</sub>	V <sub>DS</sub> ≤ -5V, V <sub>GS</sub> =-10V	-10			A
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-2.6A		90	110	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-2.0A		100	125	
		V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-1.2A		135	150	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =-5V, I <sub>D</sub> =-4.0A		10		S
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =-1.7A, V <sub>GS</sub> =0V		-0.7	-1.3	V
<b>Dynamic</b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =-15V, V <sub>GS</sub> =-4.5V I <sub>D</sub> ≡-2.0A		4	6	nC
Gate-Source Charge	Q <sub>gs</sub>			0.6		
Gate-Drain Charge	Q <sub>gd</sub>			1.5		
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V f=1MHz		230		pF
Output Capacitance	C <sub>oss</sub>			40		
Reverse Transfer Capacitance	C <sub>rss</sub>			25		
Turn-On Time	t <sub>d(on)</sub>	V <sub>DD</sub> =-15V, R <sub>L</sub> =15Ω I <sub>D</sub> ≡-1.0A, V <sub>GEN</sub> =-10V R <sub>G</sub> =6Ω		5	10	ns
	t <sub>r</sub>			8	15	
Turn-Off Time	t <sub>d(off)</sub>			15	30	
	t <sub>f</sub>			15	30	

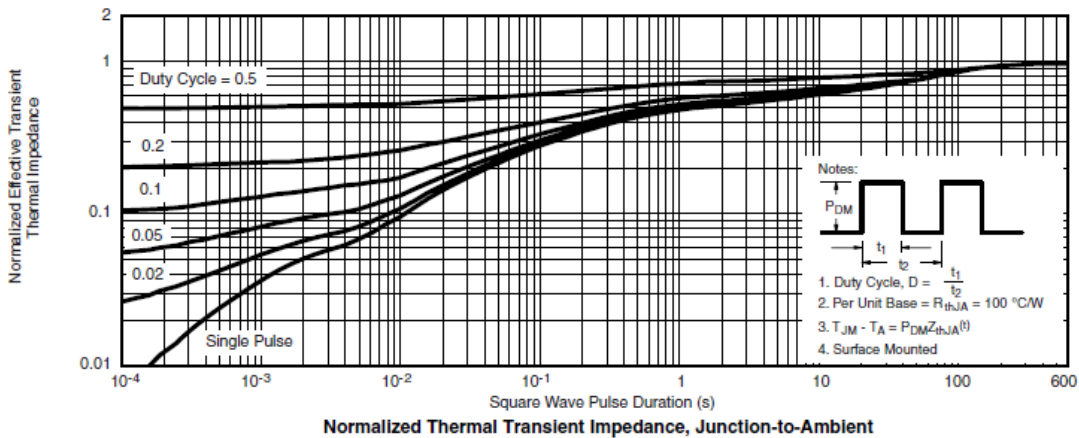
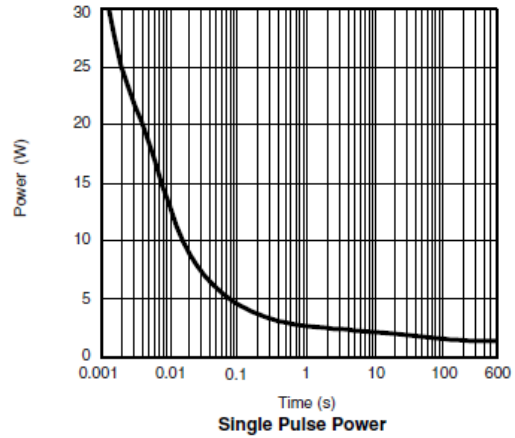
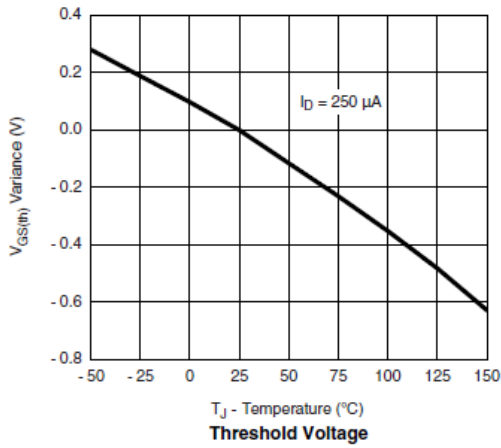
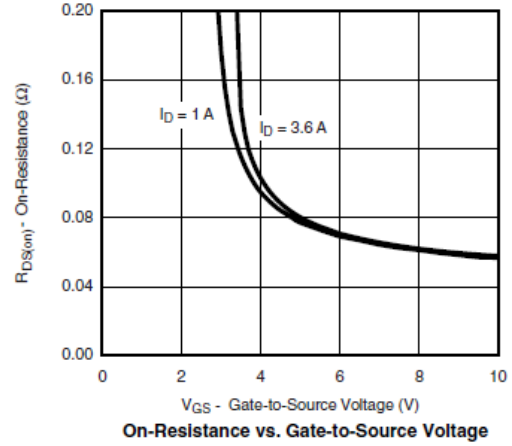
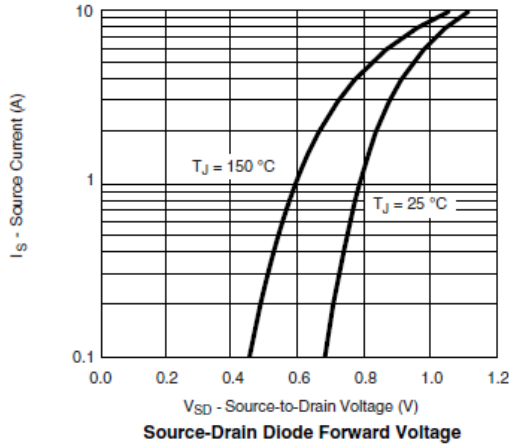


## Typical Characteristics ( N-Channel )





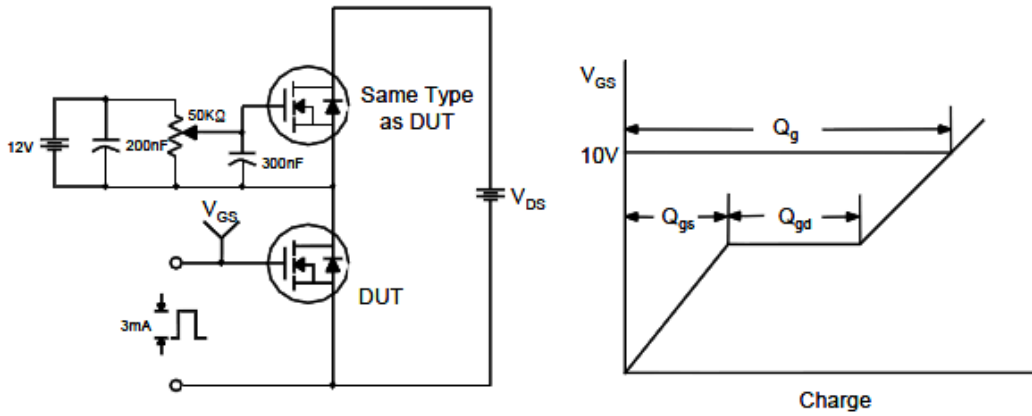
### Typical Characteristics ( N-Channel )



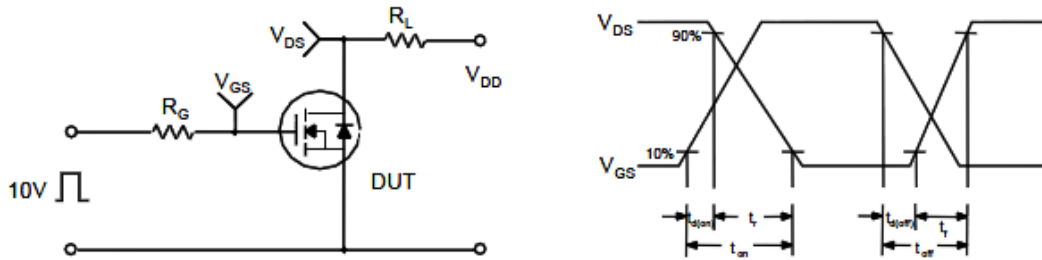


**Typical Characteristics ( N-Channel )**

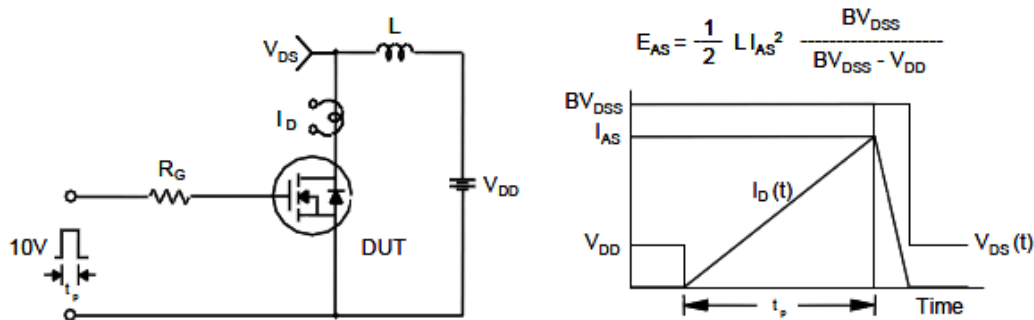
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

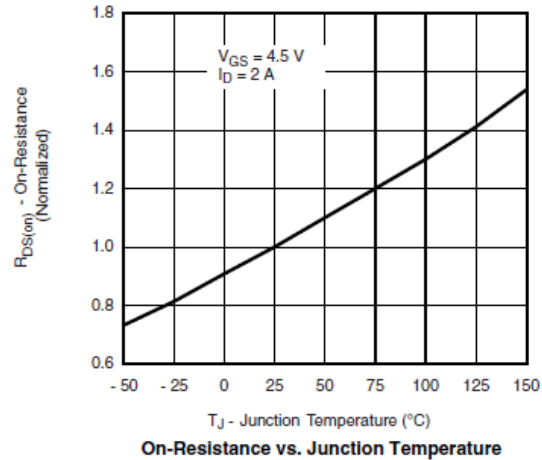
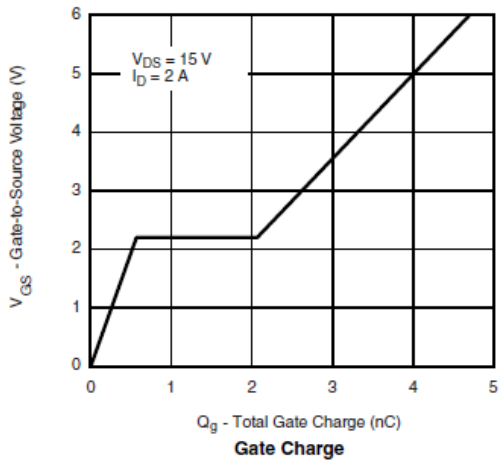
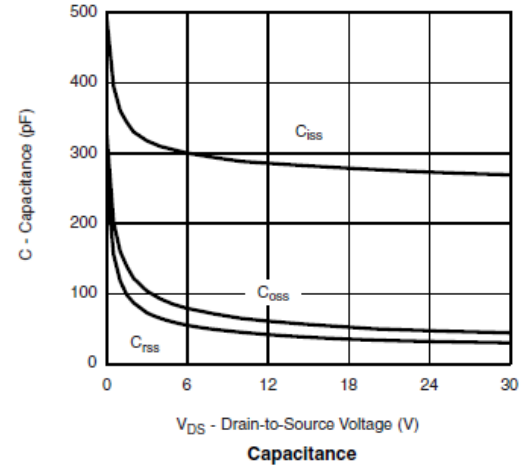
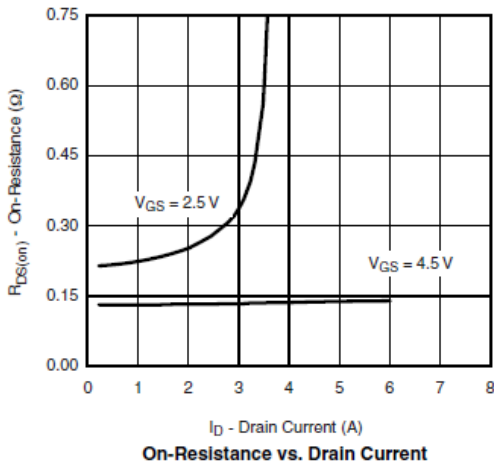
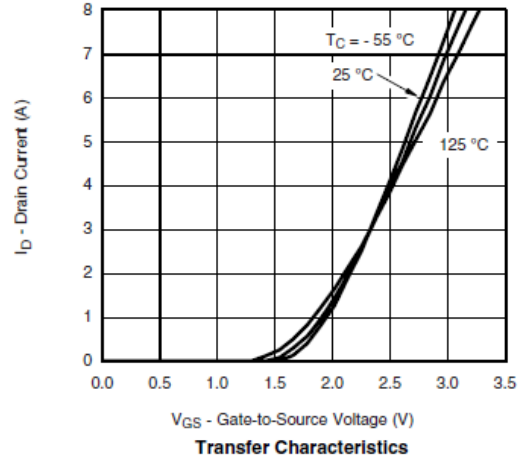
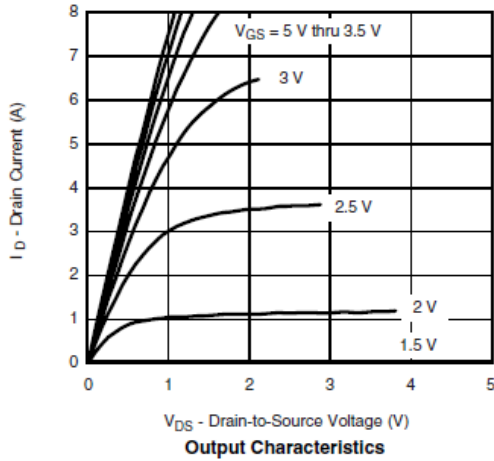


Unclamped Inductive Switching Test Circuit & Waveforms





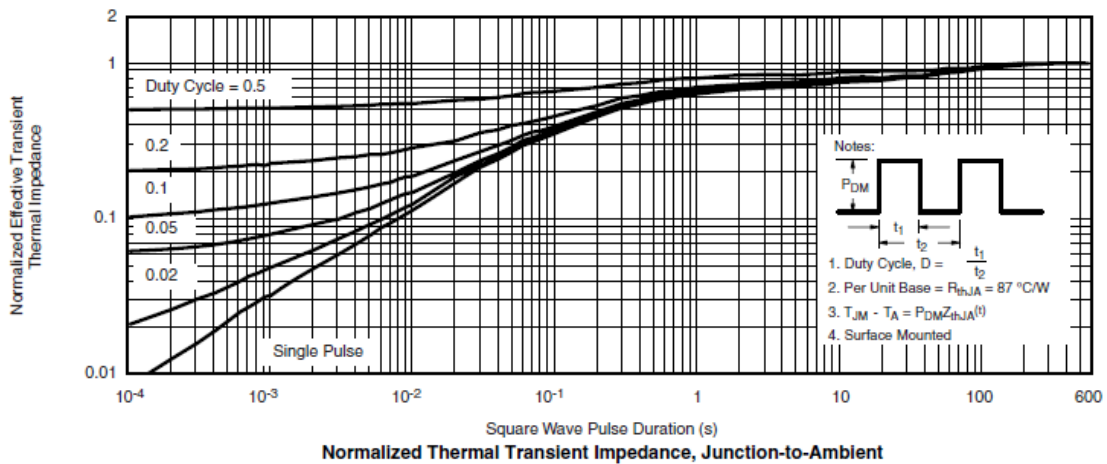
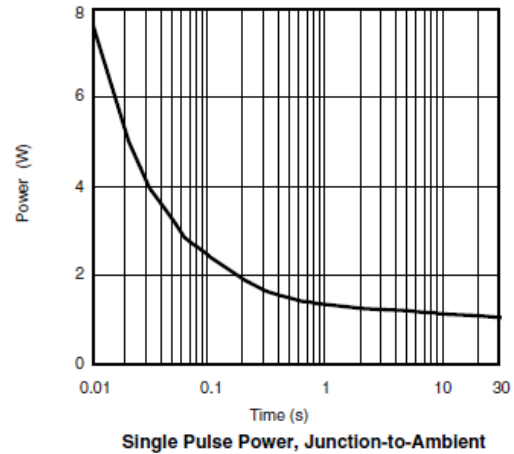
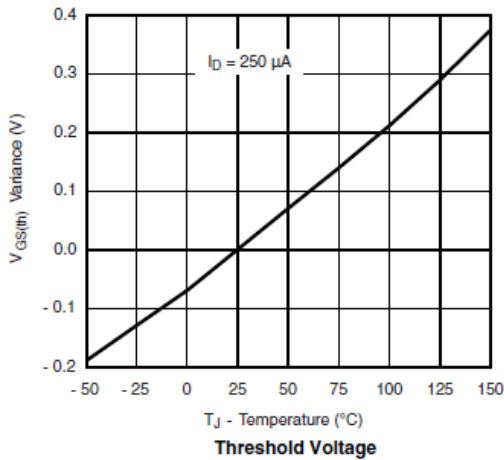
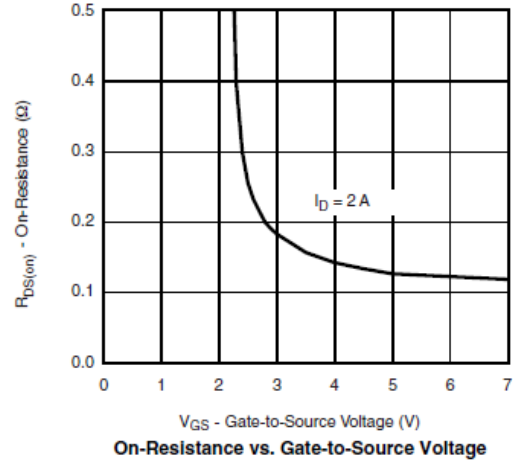
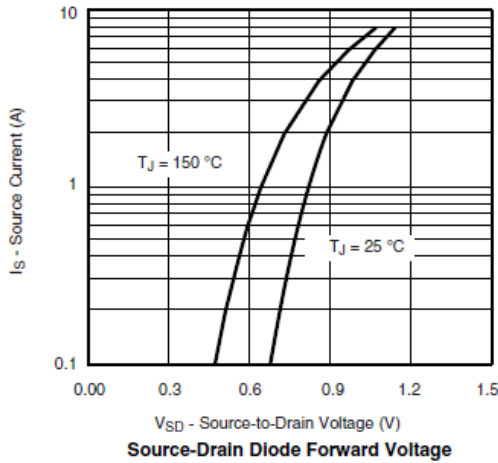
## Typical Characteristics ( P-Channel )







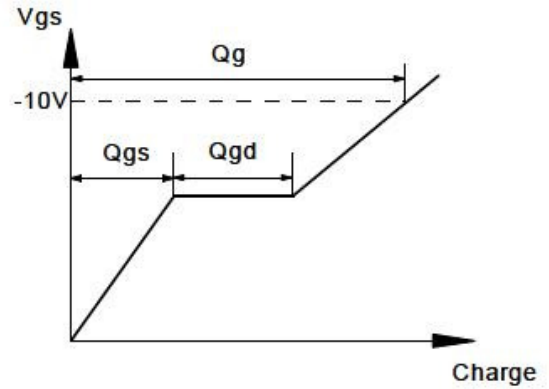
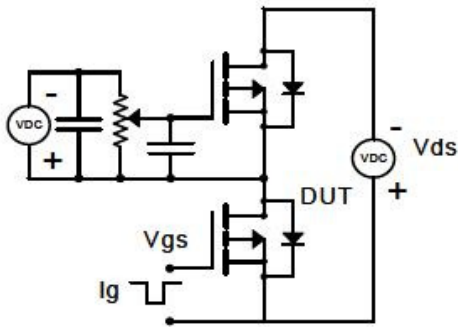
**Typical Characteristics ( P-Channel )**



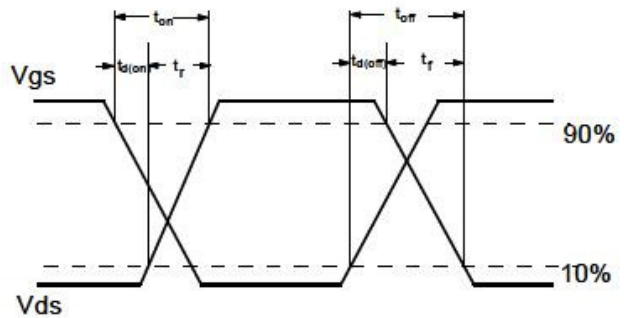
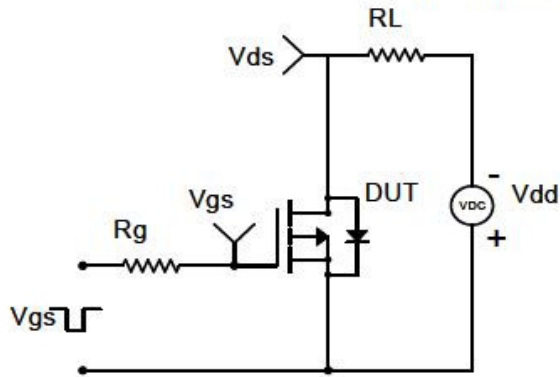


**Typical Characteristics**

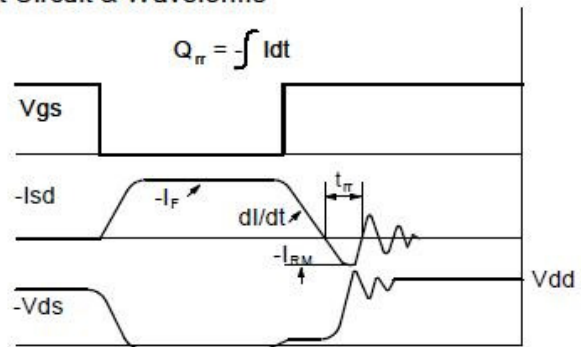
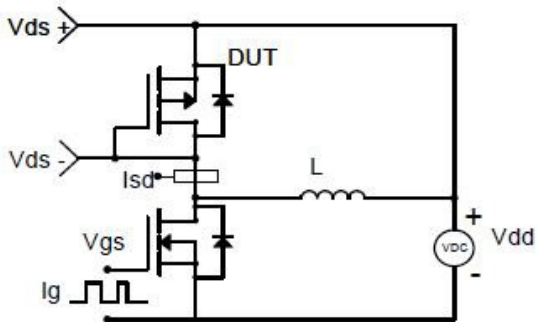
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

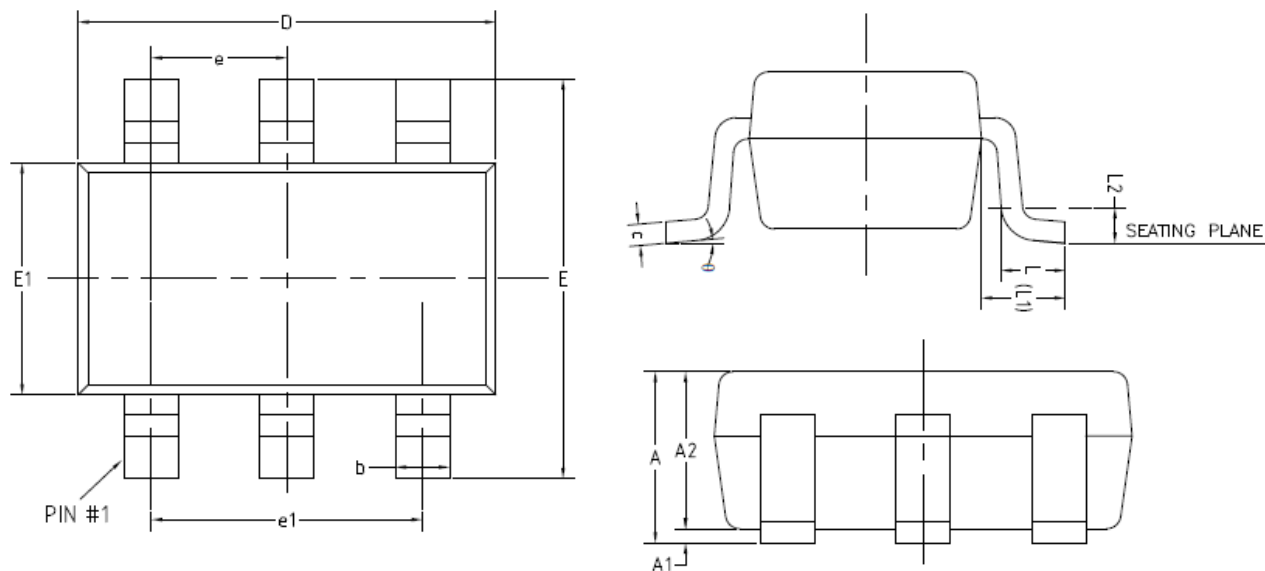


Diode Recovery Test Circuit & Waveforms





**Package Information ( TSOP-6 )**



COMMON DIMENSIONS  
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	0.70	—	0.90
A1	0	—	0.10
A2	0.70	0.75	0.80
b	0.35	—	0.50
c	0.08	—	0.20
D	2.82	2.92	3.02
E	2.65	2.80	2.95
E1	1.60	1.65	1.70
e	0.95(BSC)		
e1	1.90(BSC)		
L	0.30	0.45	0.60
L1	0.59REF		
L2	0.25BSC		
$\theta$	0°	—	8°

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